

2SA814 2SA815

SILICON PNP EPITAXIAL BASE MESA TYPE

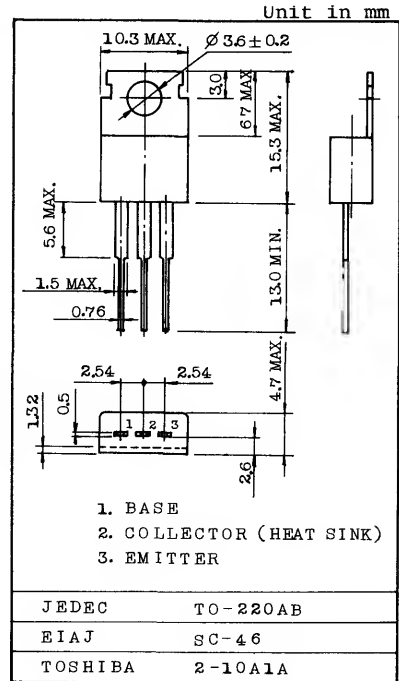
MEDIUM POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

- High Breakdown Voltage: $V_{CE0} = -120V$ (2SA814)
: $V_{CE0} = -100V$ (2SA815)
- Complementary to 2SC1624 and 2SC1625.

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	2SA814	-120	V
	2SA815	-100	
Collector-Emitter Voltage	2SA814	-120	V
	2SA815	-100	
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1	A
Emitter Current	I_E	1	A
Collector Power Dissipation ($T_c = 25^\circ C$)	P_C	15	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Mounting Kit No.: AC75
Weight : 1.9g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$	-	-	-1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$	-	-	-1.0	μA
Collector-Emitter Breakdown Voltage	2SA814	$V_{(BR)CE0}$ $I_C = -10mA, I_B = 0$	-120	-	-	V
			-100	-	-	
Emitter-Base Breakdown Voltage	$V_{(BE)EBO}$	$I_E = -1mA, I_C = 0$	-5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE} = -5V, I_C = -150mA$	70	-	240	
	$h_{FE(2)}$	$V_{CE} = -5V, I_C = -500mA$	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA$	-	-	-0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = -5V, I_C = -500mA$	-	-	-1.0	V
Transition Frequency	f_T	$V_{CE} = -5V, I_C = -150mA$	10	30	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	-	30	-	pF

Note: $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

TOSHIBA CORPORATION

